

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application: Furukawa, et al

Group Art Unit: 2823

Serial No.: 09/599,783

Examiner: Julio J. Maldonado

Filed: 06/22/2000

Docket No.: BU9-99-197

Title: Method For Etching A Semiconductor Substrate Using Germanium Hard Mask

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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Request for Reconsideration

Sir:

This Request for reconsideration is in response to the Notice of Drawing Inconsistency with Specification mailed November 29, 2004.

In the Specification

Please add the following text between lines 19 and 20 of page 3:

FIG. 7 depicts FIG. 6 after portions of the substrate in FIG. 6 have been etched, in accordance with the present invention.

FIG. 8 depicts a semiconductor device that may be formed on the substrate of FIG. 7, in accordance with the present invention.

Please treat as 312 amendment and enter

*OC
1/21/2005*

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